

This diagram shows a cross-sectional view of a semiconductor device 30. The device is built on a substrate 32, which consists of several layers: 34, 36, 38, 42, 46, 50, and 57. Two vertical structures 48 are formed, each with a top layer 52 and a side layer 55. A central trench 53 is located between these structures. The device is shown in a cross-sectional view with various layers and structures labeled with reference numerals.

FIGURE 2

FIGURE 5